TOSHIBA Field Effect Transistor Silicon N-Channel MOS Type (U-MOSIV)

TPCA8026

Lithium-Ion Battery Applications Notebook PC Applications Portable Equipment Applications

- Small footprint due to a small and thin package
- Low drain-source ON-resistance: $RDS(ON) = 1.8 \text{ m}\Omega \text{ (typ.)}$
- High forward transfer admittance: $|Y_{fs}| = 100 \text{ S (typ.)}$
- Low leakage current: $IDSS = 10 \mu A (max) (VDS = 30 V)$
- Enhancement mode: $V_{th} = 1.3$ to 2.5 V ($V_{DS} = 10$ V, $I_{D} = 1$ mA)

Absolute Maximum Ratings (Ta = 25°C)

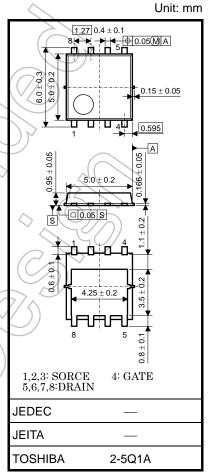
Characteristic		Symbol	Rating	Unit
Drain-source voltage		V_{DSS}	30	V
Drain-gate voltage ($R_{GS} = 20 \text{ k}\Omega$)		V _{DGR}	30	V
Gate-source voltage		V _{GSS}	±20	/
Drain current	DC (Note 1)	ID	45	A
	Pulsed (Note 1)	I _{DP}	135	^
Drain power dissipation	on $(Tc = 25^{\circ}C)$	(PD \	45	(w
Drain power dissipation	on (t = 10 s) (Note 2a)	D D	2.8	K
Drain power dissipation	on (t = 10 s) (Note 2b)	PD	1.6	W
Single-pulse avalanche energy (Note 3)		EAS	263	mJ
Avalanche current		I _{AR}	45	Α
Repetitive avalanche energy (Tc = 25°C) (Note 4)		EAR	3.4	mJ
Channel temperature		T _{ch}	150	°C
Storage temperature	range	T _{stg}	-55 to 150	°C

Note: For Notes 1 to 4, refer to the next page.

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating

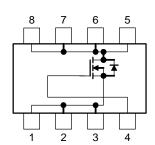
Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

This transistor is an electrostatic-sensitive device. Handle with care.



Weight: 0.069 g (typ.)

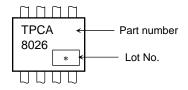
Circuit Configuration



Thermal Characteristics

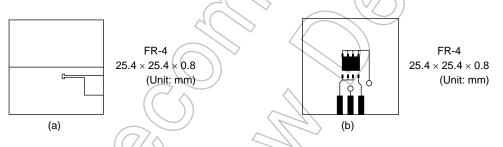
Characteristic	Symbol	Max	Unit
Thermal resistance, channel to case (Tc = 25°C)	R _{th (ch-c)}	2.78	°C/W
Thermal resistance, channel to ambient (t = 10 s) (Note 2a)	R _{th (ch-a)}	44.6	°C/W
Thermal resistance, channel to ambient (t = 10 s) (Note 2b)	R _{th (ch-a)}	78.1	°C/W

Marking (Note 5)



Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: (a) Device mounted on a glass-epoxy board (a) (b) Device mounted on a glass-epoxy board (b)



Note 3: $V_{DD} = 24 \text{ V}$, $T_{ch} = 25^{\circ}\text{C}$ (initial), L = 0.1 mH, $I_{AR} \neq 45 \text{ A}$

Note 4: Repetitive rating: pulse width limited by maximum channel temperature

Note 5: * Weekly code: (Three digits)

Week of manufacture
(01) for the first week of the year, continuing up to 52 or 53)

Year of manufacture (The last digit of the year)

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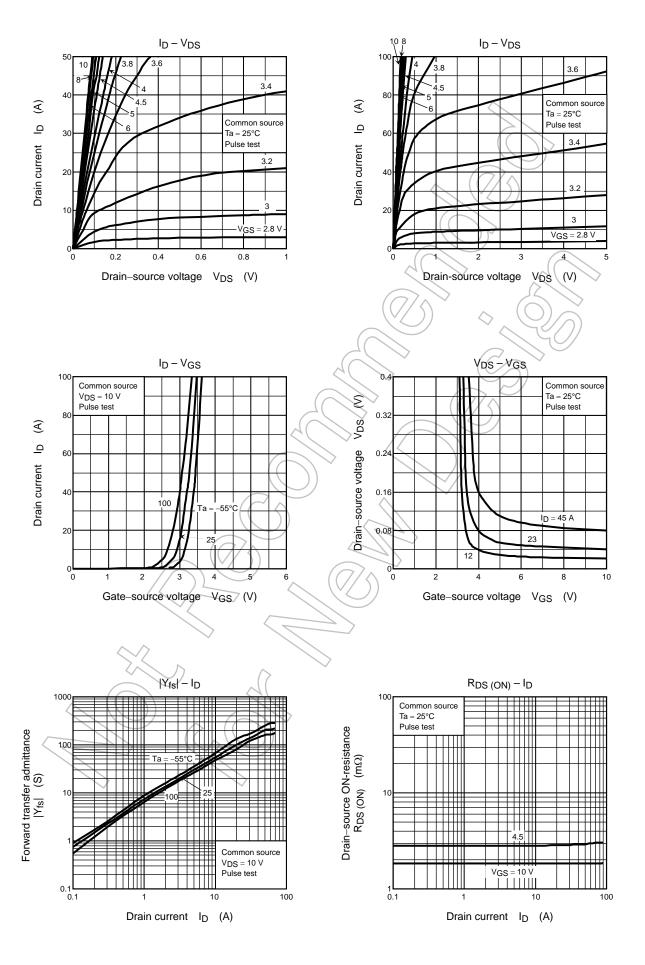
Electrical Characteristics (Ta = 25°C)

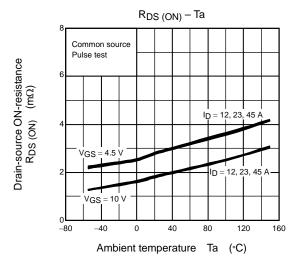
Ch	aracteristic	Symbol	Test Condition	Min	Тур.	Max	Unit	
Gate leakage cui	rrent	I _{GSS}	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$	_	_	±100	nA	
Drain cutoff curre	ent	I _{DSS}	V _{DS} = 30 V, V _{GS} = 0 V	_	_	10	μА	
Drain-source breakdown voltage		V (BR) DSS	$I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}$	30	_	_	V	
		V (BR) DSX	$I_D = 10 \text{ mA}, V_{GS} = -20 \text{ V}$	10		_		
Gate threshold ve	oltage	V_{th}	V _{DS} = 10 V, I _D = 1 mA	1.3) /_	2.5	V	
Drain-source ON-resistance		R _{DS} (ON)	V _{GS} = 4.5 V, I _D = 23 A	,7 <u>~</u>	2.7	4.5	- mΩ	
			V _{GS} = 10 V, I _D = 23 A	\rightarrow	1.8	2.2		
Forward transfer	admittance	Y _{fs}	V _{DS} = 10 V, I _D = 23 A	50	100	_	S	
Input capacitance		C _{iss}		_	4200	_		
Reverse transfer capacitance		C _{rss}	$V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	_	1000	_	pF	
Output capacitan	ce	C _{oss}			1400	\rightarrow		
Switching time	Rise time	t _r	V _{GS} 10 V	-(15	> _		
	Turn-on time	t _{on}		OV-VOUT	_	200		
	Fall time	t _f	RL = 0.6	(\mathcal{E})	36	_	ns	
	Turn-off time	t _{off}	V _{DD} ≈ 15 V Duty ≤ 1%, t _w = 10 μs) —	111	_		
Total gate charge (gate-source plus		Qg		_	113	_		
Gate-source charge 1		Q _{gs1}	$V_{DD} \approx 24 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 45 \text{ A}$	_	13	_	nC	
Gate-drain ("miller") charge		Q_{gd}		_	42	_		

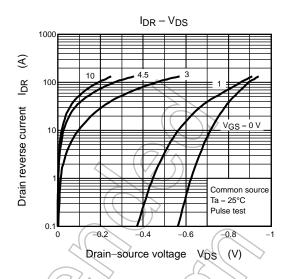
Source-Drain Ratings and Characteristics (Ta = 25°C)

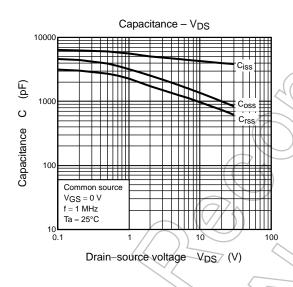
Characteristic	Symbol	Test Condition	Min	Тур.	Max	Unit
Drain reverse current Pulse (Note 1)	I _{DRP}	<u> </u>	_	_	135	Α
Forward voltage (diode)	VDSF	$I_{DR} = 45 \text{ A}, V_{GS} = 0 \text{ V}$	_	_	-1.2	V

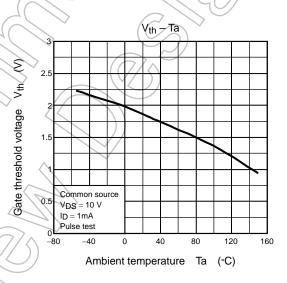


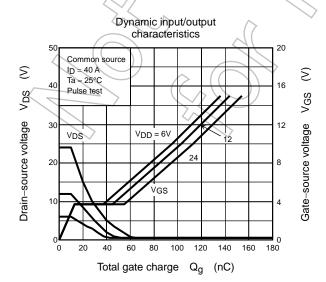






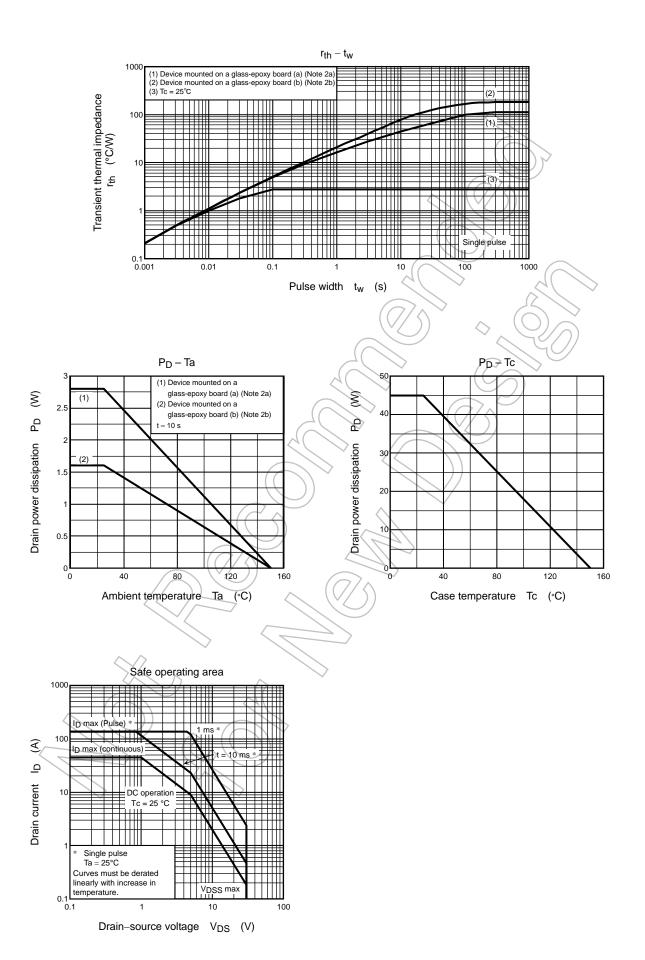






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